

General Description

The AP1662 is an active power factor control IC which is designed mainly for use as a pre-converter in electronic ballast, AC-DC adapter and off-line SMPS applications.

The IC includes an internal start-up timer for stand-alone applications, a one-quadrant multiplier to realize near unity power factor and a zero current detector to ensure DCM boundary conduction operation.

The totem pole output stage is capable of driving power MOSFET with 600mA source current and 800mA sink current.

Designed with advanced BiCMOS process, the AP1662 features low start-up current, low operation current and low power dissipation. The AP1662 also has rich protection features including over-voltage protection, input under-voltage lockout with hysteresis and multiplier output clamp to limit maximum peak current.

The AP1662 meets IEC61000-3-2 standard even at one-quadrant load and THD lower than 10% at high-end line voltage and full load.

The IC is available in SOIC-8 and DIP-8 packages.

Features

- Comply with IEC61000-3-2 Standard
- Proprietary Design for Minimum THD
- Zero Current Detection Control for DCM Boundary Conduction Mode
- Adjustable Output Voltage with Precise Over-voltage Protection
- Low Start-up Current with 40µA Typical Value
- Low Quiescent Current with 2.5mA Typical Value
- 1% Precision Internal Reference Voltage (a) $T_J=25^{\circ}C$
- Internal Start-up Timer
- Disable Function for Reduced Current Consumption
- Totem Pole Output with 600mA Source and 800mA Sink Current Capability
- Under-voltage Lockout with 2.5V Hysteresis

Applications

- Electronic Ballast
- AC-DC Adapter
- Off-line SMPS
- Single Stage PFC LED Driver

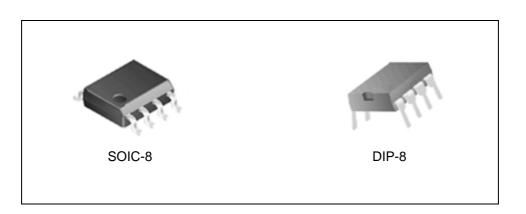
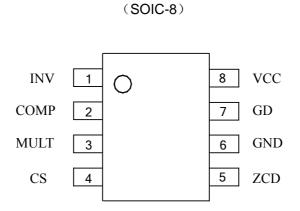


Figure 1. Package Types of AP1662



M Package

Pin Configuration





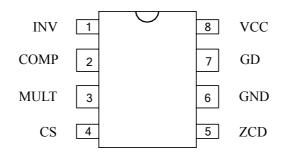


Figure 2. Pin Configuration of AP1662 (Top View)



Pin Description

Pin Number	Pin Name	Function
1	INV	Inverting input of the error amplifier
2	COMP	Output of the error amplifier
3	MULT	Input of the multiplier
4	CS	Input of the current control loop comparator
5	ZCD	Zero current detection input. If it is connected to GND, the device is disabled
6	GND	Ground. Current return for gate driver and control circuits of the IC
7	GD	Gate driver output
8	VCC	Supply voltage of gate driver and control circuits of the IC

Functional Block Diagram

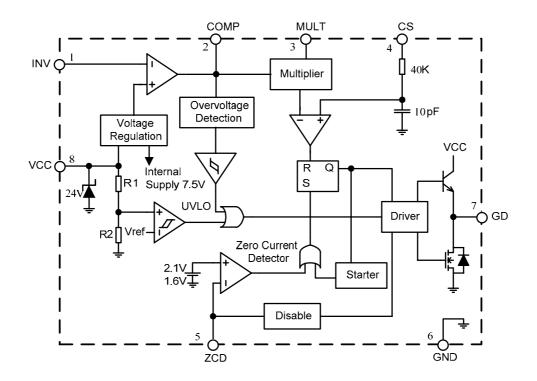
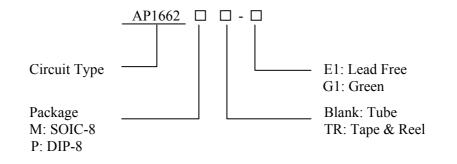


Figure 3. Functional Block Diagram of AP1662



Ordering Information



Daakaga	Temperature	Part Number		Mark	Packing		
Package	Range	Lead Free	Green	Lead Free	Green	Туре	
SOIC-8	-40 to 105°C	AP1662M-E1	AP1662M-G1	1662M-E1	1662M-G1	Tube	
		AP1662MTR-E1	AP1662MTR-G1	1662M-E1	1662M-G1	Tape & Reel	
DIP-8	-40 to 105°C	AP1662P-E1	AP1662P-G1	AP1662P-E1	AP1662P-G1	Tube	

BCD Semiconductor's Pb-free products, as designated with "E1" suffix in the part number, are RoHS compliant. Products with "G1" suffix are available in green packages.



Absolute Maximum Ratings (Note 1)

Parameter	Symbol	Value		Unit
Power Supply Voltage	V _{CC}	Self-limited		V
Operating Supply Current	I _{CC}	30		mA
Input/Output of Error Amplifier, Input of Multiplier	V _{INV} , V _{COMP} , V _{MULT}	-0.3 to 7		V
Current Sense Input	V _{CS}	-0.3 to 7		V
Zana Current Datastan Innut	T	Source	-50	mA
Zero Current Detector Input	I _{ZCD}	Sink	10	ША
Power Dissipation and Thermal	P _{TOT}	DIP-8	1	W/
characteristics @ $T_A=50^{\circ}C$		SOIC-8	0.65	— W
Thermal Resistance	R _{θJA} –	DIP-8	100	⁹ C/W
(Junction to Ambient)		SOIC-8	150	• C/W
Operating Junction Temperature	TJ	-40 to 150		° C
Storage Temperature Range	T _{STG}	-65 to 150		° C
Lead Temperature (Soldering, 10 Seconds)	T _{LEAD}	260		°C
ESD (Human Body Model)	V _{ESD(HBM)}	3000		V
ESD (Machine Model)	V _{ESD(MM)}	200		V

Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.



Electrical Characteristics

 V_{CC} =12V, T_J =-25°C to 125°C, C_O =1nF, unless otherwise specified.

Parame	ter	Symbol	Test Conditions	Min	Тур	Max	Unit
Under V	Voltage Lockou	t Section					
Turn-on	Threshold	V _{CC-ON}	V _{CC} Rising	11	12	13	V
Turn-off	Threshold	V _{CC-OFF}	V _{CC} Falling	8.7	9.5	10.3	V
Hysteresi	S	V _{CC-HYS}		2.2	2.5	2.8	V
V _{CC} Operating Range		V _{CC}	After turn-on	10.3		22	v
Zener Voltage		Vz	I _{CC} =20mA	22	24		V
Total S	upply Current	Section					
Start-up (Current	I _{START-UP}	V _{CC} =11V before turn-on		40	70	μA
			Frequency=70kHz		3.5	5	
Operating Supply Current		I _{CC}	In OVP condition V _{INV} =2.7V		1.4	2.2	mA
Quiescent Current		I_Q	After turn on		2.5	3.75	mA
Quiescent Current		I _Q	$V_{ZCD} \leq 150 \text{mV}, V_{CC} > V_{CC-OFF}$			2.2	mA
			$V_{ZCD} \leq 150 \text{mV}, V_{CC} < V_{CC-OFF}$	20	50	90	μΑ
Error A	mplifier Section	n					
Voltage Feedback Input Threshold		V _{INV}	$T_J = 25^{\circ}C$	2.465	2.5	2.535	17
			10.3V <v<sub>CC<20V</v<sub>	2.44		2.56	V
Line Reg	ulation		V _{CC} =10.3V to 20V		2	5	mV
Input Bia	s Current	I _{INV}	V _{INV} =0 to 3V		-0.1	-1	μΑ
Voltage Gain		G _V	Open Loop	60	80		dB
Gain Bandwidth		G _B			1		MHz
Output Voltage	Upper Clamp Voltage	V _{COMP-H}	I _{SOURCE} =0.5mA	5.15	5.55	5.85	V
	Lower Clamp Voltage	V _{COMP-L}	I _{SINK} =0.5mA	2.1	2.25	2.4	v
Output	Source Current	I _{COMP-H}	$V_{COMP}=4V, V_{INV}=2.4V$	-2	-4	-8	mA
Current	Sink Current	I _{COMP-L}	V _{COMP} =4V, V _{INV} =2.6V	2.5	4.5		



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Electrical Characteristics (Continued)

 V_{CC} =12V, T_J =-25°C to 125°C, C_O =1nF, unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Multiplier Section							
Linear Input Voltage Range	V _{MULT}		0 to 3	0 to 3.5		V	
Output Maximum Slope	$\begin{array}{c} \bigtriangleup V_{\text{CS}} / \\ \bigtriangleup V_{\text{MULT}} \end{array}$	V _{MULT} : 0 to 0.5V, V _{COMP} =Upper Clamp Voltage	1.65	1.9			
Gain	k	V _{MULT} =1V, V _{COMP} =4V	0.6	0.75	0.9	1/V	
Current Sense Sect	ion						
Input Bias Current	I _{CS}	V _{CS} =0V			-1	μΑ	
Current Sense Offset	V _{CS-OFFSET}	V _{MULT} =0V		30		mV	
Voltage	· C3-0113E1	V _{MULT} =2.5V		5		/	
Current Sense Reference Clamp	V _{CS-CLAMP}	$V_{COMP} = Upper Clamp$ Voltage, $V_{MULT} = 2.5V$	1.6	1.7	1.8	V	
Delay to Output	t _{d(H-L})			200	350	ns	
Zero Current Detec	tion Section	n					
Arming Voltage (positive-going edge)	V _{ZCDA}	(Note 2)		2.1		V	
Triggering Voltage (negative-going edge)	V _{ZCDT}	(Note 2)		1.6		V	
	V _{ZCD-H}	I _{ZCD} =20µA	4.5	5.1	5.9	v	
Upper Clamp Voltage		I _{ZCD} =3mA	4.7	5.2	6.1		
Lower Clamp Voltage	V _{ZCD-L}	I_{ZCD} = -3mA	0.3	0.65	1	V	
Source Current Capability	I _{ZCD-SR}		-2.5		-10	mA	
Sink Current Capability	I _{ZCD-SN}		3			mA	
Sink Bias Current	I _{ZCD-B}	$1V \leq V_{ZCD} \leq 4.5 V$		2		μΑ	
Disable Threshold	V _{ZCD-DIS}		150	200	250	mV	
Disable Hysteresis	V _{ZCD-HYS}			100		mV	
Restart Current After Disable	I _{ZCD-RES}	V _{ZCD} <v<sub>DIS, V_{CC}>V_{CC-OFF}</v<sub>	-80	-120		μΑ	

Note 2: Limits over the full temperature are guaranteed by design, but not tested in production.



AP1662

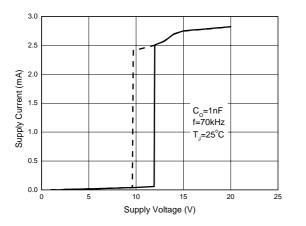
Electrical Characteristics (Continued)

 V_{CC} =12V, T_J =-25°C to 125°C, C_O =1nF, unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Drive Output Section						
	V _{OH}	I _{GD-SOURCE} =200mA		2.5	3	
Dropout Voltage		I _{GD-SOURCE} =20mA		2	2.8	V
	V _{OL}	I _{GD-SINK} =200mA		0.9	1.9	
Output Voltage Rise Time	t _R			40	80	ns
Output Voltage Fall Time	$t_{\rm F}$			30	70	ns
Output Clamp Voltage	V _{O-CLAMP}	$I_{GD-SOURCE}=5mA$ $V_{CC}=20V$	9	11	13	V
UVLO Saturation	V _{OS}	V _{CC} =0 to V _{CC-ON} , I _{SINK} =10mA			1.1	V
Output Over Voltage Section						
OVP Triggering Current	I _{OVP}		35	40	45	μΑ
Static OVP Threshold	V _{OVP_TH}		2.1	2.25	2.4	V
Starter						
Start Timer Period	t _{START}		75	130	300	μs



Typical Performance Characteristics



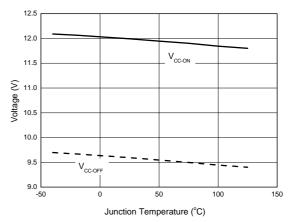


Figure 4. Supply Current vs. Supply Voltage

Figure 5. Start-up & UVLO vs. $T_{\rm J}$

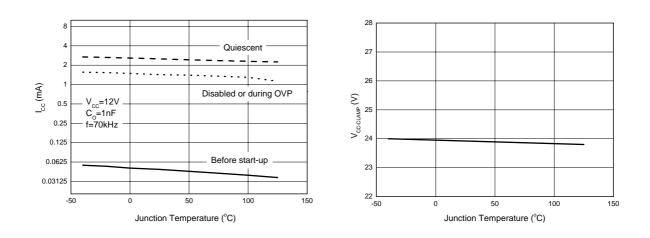
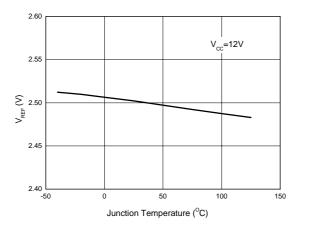


Figure 6. I_{CC} Consumption vs. T_J

Figure 7. V_{CC} Zener Voltage vs. T_J





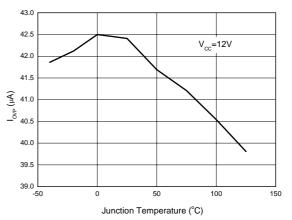


Figure 8. Feedback Reference Voltage vs. $T_{\rm J}$

Figure 9. OVP Current vs. T_J

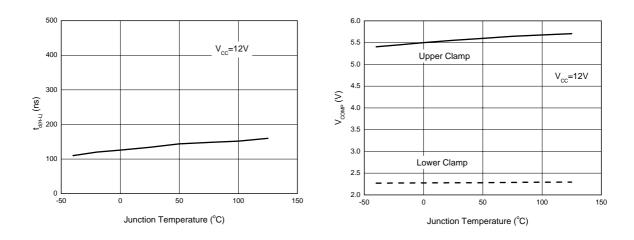
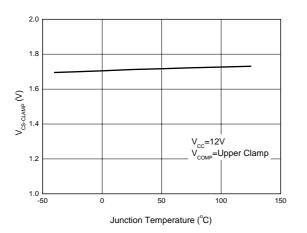


Figure 10. Delay-to-Output vs. T_J

Figure 11. E/A Output Clamp Levels vs. $T_{\rm J}$





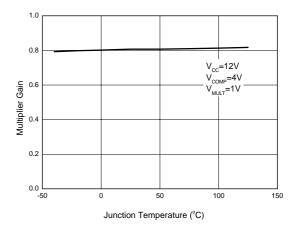


Figure 12. V_{CS-CLAMP} vs. T_J

Figure 13. Multiplier Gain vs. TJ

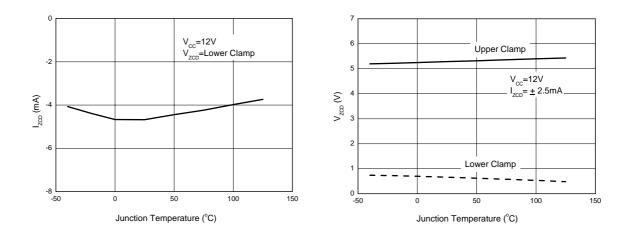


Figure 14. ZCD Source Capability vs. $T_{\rm J}$



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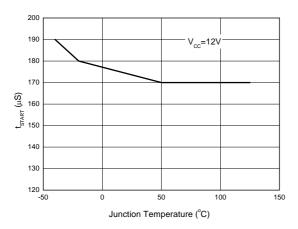


Figure 16. Start-up Timer vs. TJ

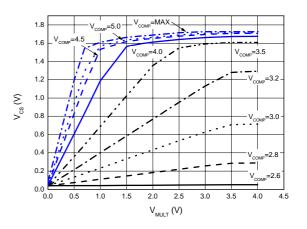


Figure 17. Multiplier Characteristics

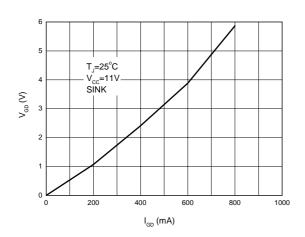


Figure 18. Gate-driver Output Low Saturation

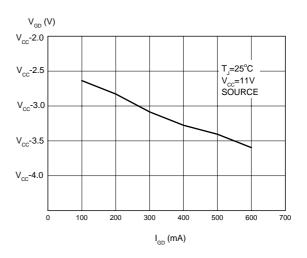


Figure 19. Gate-driver Output High Saturation



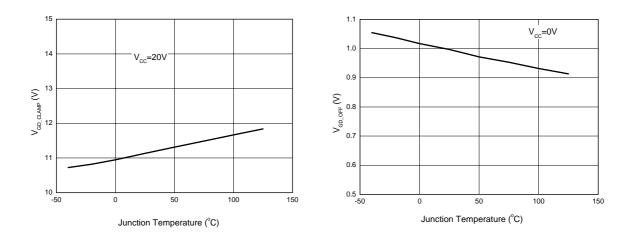


Figure 20. Gate-driver Clamp vs. T_J

Figure 21. UVLO Saturation vs. $T_{\rm J}$



Functional Block Description

AP1662 is a high performance power factor correction controller which operates in DCM boundary conduction mode. The PFC converter's switch will be turned on when the inductor current reduces to zero and turned off when the sensed inductor current reaches the required reference which is decided by the output of multiplier.

Error Amplifier and Over-Voltage Protection

The error amplifier regulates the PFC output voltage. The internal reference on the non-inverting input of the error amplifier is 2.5V. The error amplifier's inverting input (INV) is connected to an external resistor divider which senses the output voltage. The output of error amplifier is one of the two inputs of multiplier. A compensation loop is connected outside between INV and the error amplifier output. Normally, the compensation loop bandwidth is set very low to realize high power factor for PFC converter.

To make the over voltage protection fast, the internal OVP function is added. If the output over voltage happens, excess current will flow into the output pin of the error amplifier through the feedback compensation capacitor. (see Figure 22) The AP1662 monitors the current flowing into the error amplifier output pin. When the detected current is higher than 40μ A, the dynamic OVP is triggered. The IC will be

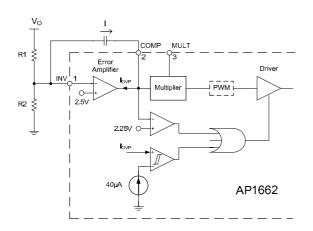


Figure 22. Error Amplifier and OVP Block

disabled and the drive signal is stopped. If the output over voltage lasts so long that the output of error amplifier goes below 2.25V, static OVP will take place. Also the IC will be disabled until the output of error amplifier goes back to its linear region. R1 and R2 (see Fig. 22) will be selected as below:

$$\frac{R1}{R2} = \frac{V_o}{2.5V} - 1$$

 $R1 = \frac{\Delta v_{OVP}}{40\,\mu A}$

Multiplier

The multiplier has two inputs. One (Pin 3) is the divided AC sinusoidal voltage which makes the current sense comparator threshold voltage vary from zero to peak value. The other input is the output of error amplifier (Pin 2). In this way, the input average current wave will be sinusoidal as well as reflects the load status. Accordingly a high power factor and good THD are achieved. The multiplier transfer character is designed to be linear over a wide dynamic range, namely, 0V to 3V for Pin 3 and 2V to 5.8V for Pin 2. The relationship between the multiplier output and inputs is described as below equation:

$$V_{CS} = k \times (V_{COMP} - 2.5) \times V_{MULT}$$

where V_{CS} (Multiplier output) is the reference for the current sense, k is the multiplier gain, V_{COMP} is the voltage on pin 2 (error amplifier output) and V_{MULT} is the voltage on pin 3.

Current Sense/Current Sense Comparator

The PFC switch's turn-on current is sensed through an external resistor in series with the switch. When the sensed voltage exceeds the threshold voltage (the multiplier output), the current sense comparator will become low and the external MOSFET will be turned off. This insures a cycle-by-cycle current mode control operation. The maximum current sense reference is 1.8V. The max value usually happens at startup process or abnormal conditions such as short load.



Functional Block Description

(Continued)

Zero Current Detection

AP1662 is a DCM boundary conduction current mode PFC controller. Usually, the zero current detection (ZCD) voltage signal comes from the auxiliary winding of the boost inductor. When the ZCD pin voltage decreases below 1.6V, the gate drive signal becomes high to turn on the external MOSFET. 500mV of hysteresis is provided to avoid false triggering. The ZCD pin can be used for disabling the IC. Making its voltage below 0.15V or short to the ground will disable the device thus reduce the IC supply current consumption.

Typical Application

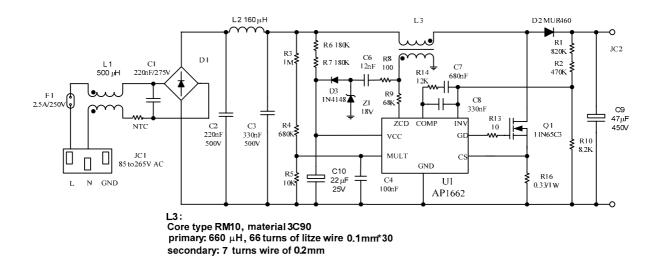


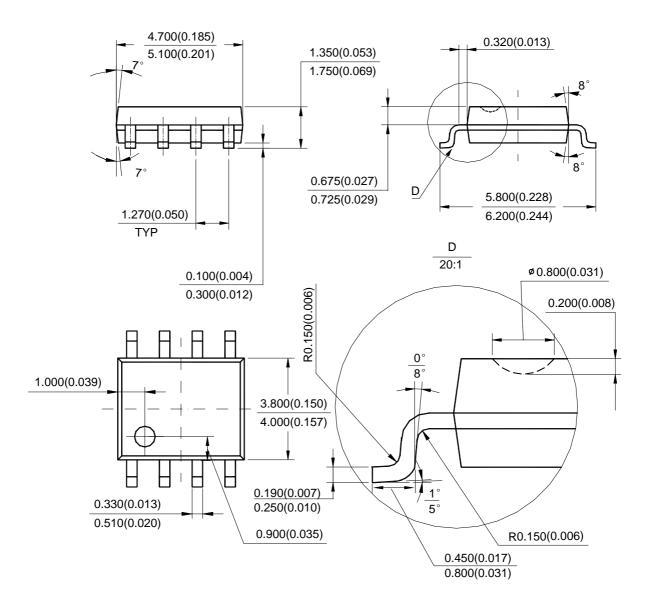
Figure 23. 85 to 265V Wide Range Input 90W PFC Demo Board Electrical Schematic Circuit



Mechanical Dimensions

Unit: mm(inch)





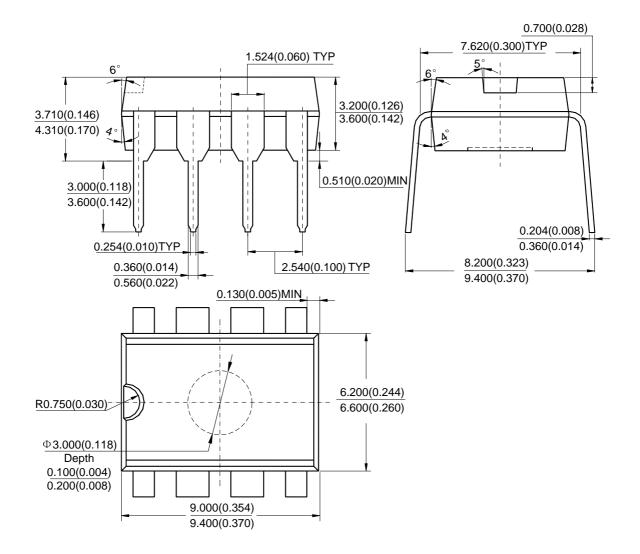
Note: Eject hole, oriented hole and mold mark is optional.



Mechanical Dimensions (Continued)

DIP-8

Unit: mm(inch)



Note: Eject hole, oriented hole and mold mark is optional.

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